

**AMENDMENTS TO THE CLAIMS**

Please cancel claims 1-4; amend claim 5; and add new claims 8-10 as follows:

Claims 1-4 (canceled)

Claim 5 (currently amended) A process for forming a photoresist pattern, the process comprising comprises:

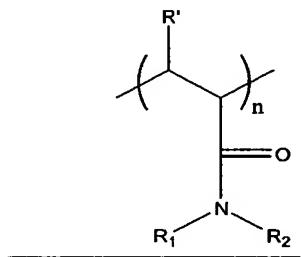
(a) coating a photoresist composition on an underlying layer to form a photoresist film;

(b) coating ~~the~~ a photoresist overcoating composition ~~of claim 1~~ on the photoresist film to form an overcoating film; wherein the photoresist overcoating composition comprises:

a solvent, and

a compound of Formula 1,

Formula 1



wherein

R' is H or CH<sub>3</sub>,

R<sub>1</sub> and R<sub>2</sub> individually are H or a C<sub>1</sub>-C<sub>3</sub> alkyl;

(c) exposing the resultant structure;

(d) baking the resultant structure; and

(e) developing the resultant structure.

Claim 6 (original) The process according to claim 5, wherein the photoresist composition includes a chemically amplified photoresist resin.

Claim 7 (original) The process according to claim 5, wherein the light source of the exposing step is selected from the group consisting of ArF(193 nm), KrF(248 nm), F2(157 nm), EUV(13 nm), E-beam, X-ray and ion beam.

Claim 8 (new) The process according to claim 5, wherein the compound of Formula 1 is poly(N,N-dimethylacrylamide).

Claim 9 (new) The process according to claim 5, wherein the solvent of the photoresist overcoating composition comprises distilled water.

Claim 10 (new) The process according to claim 5, wherein the compound of Formula 1 is present in an amount ranging from 1 to 30 wt% to the solvent.